

## Charge collection test and TCAD simulation of OVERMOS, a CMOS 180nm MAPS detector

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We will present results of charge collection of OVERMOS, a high resistivity TJ 180nm CMOS MAPS, obtained using 1064 nm calibrated laser source.

Result include charge collection over pixel region, sampled with 5 um resolution, and charge collection time.

Test results are compared with 3D TCAD optical simulations, taking into account SiO<sub>2</sub> and CoSi<sub>2</sub> attenuation.

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